

GaAs MMIC SP4T NON-REFLECTIVE SWITCH. DC - 8 GHz

Typical Applications

The HMC344 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation

Features

Broadband Performance: DC - 8 GHz

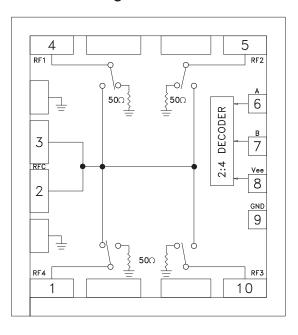
Non-Reflective Topology

Low Insertion Loss: 1.8 dB @ 6 GHz

Integrated 2:4 TTL Decoder

Small Size: 1.08 x 1.05 x 0.10 mm

Functional Diagram



General Description

The HMC344 is a broadband non-reflective GaAs MESFET SP4T switch chip. Covering DC to 8 GHz, this switch offers high isolation, low insertion loss, and a compact form factor. This switch also includes an on board binary decoder circuit which reduces the number of required logic control lines to two. The switch operates using a negative control voltage of 0/-5V, and requires a fixed bias of -5V. All data is tested with the chip in a 50 Ohm test fixture connected via 0.025 mm (1 mil) diameter wire bonds of minimal length 0.31 mm (12 mils). This SP4T switch is also available in SMT packaged form as the HMC344LC3.

Electrical Specifications, $T_A = +25^{\circ}$ C, With 0/-5V Control, Vee= -5V, 50 Ohm System

Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 6.0 GHz DC - 8.0 GHz		1.8 1.9	2.1 2.2	dB dB
Isolation		DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz DC - 8.0 GHz	44 37 34 30	49 42 39 35		dB dB dB dB
Return Loss "On	State"	DC - 2.0 GHz DC - 8.0 GHz	10 7	14 10		dB dB
Return Loss "Off	State"	DC - 8.0 GHz	7	10		dB
Input Power for 1 dB Compression		0.5 - 8.0 GHz	17	21		dBm
Input Third Order Intercept (Two-Tone Input Power= +7 dBm Each Tone)		0.5 - 8.0 GHz	37	40		dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)		DC - 8.0 GHz		35 150		ns ns

HMC344* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS 🖳

View a parametric search of comparable parts.

EVALUATION KITS

- · HMC344LC3 Evaluation Board.
- HMC344LH5 Evaluation Board
- · HMC344LP3 Evaluation Board.

DOCUMENTATION



Data Sheet

- HMC344 Die Data Sheet
- HMC344LC3 Data Sheet
- · HMC344LH5 Data Sheet
- HMC344LP3 Data Sheet

TOOLS AND SIMULATIONS 🖵

- HMC344 Die S-Parameters
- HMC344LC3 S-Parameters
- HMC344LH5 S-Parameters
- HMC344LP3 S-Parameters

REFERENCE MATERIALS 🖳

Quality Documentation

- Package/Assembly Qualification Test Report: 16L 3x3mm QFN Package (QTR: 11003 REV: 02)
- Package/Assembly Qualification Test Report: LC3, LC3B, LC3C (QTR: 2014-00376 REV: 01)
- · Package/Assembly Qualification Test Report: LP2, LP2C, LP3, LP3B, LP3C, LP3D, LP3F, LP3G (QTR: 2014-0364)
- Package/Assembly Qualification Test Report: Plastic Encapsulated QFN (QTR: 05006 REV: 02)
- Semiconductor Qualification Test Report: MESFET-F (QTR: 2013-00247)

DESIGN RESOURCES -



- · HMC344 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

DISCUSSIONS

View all HMC344 EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

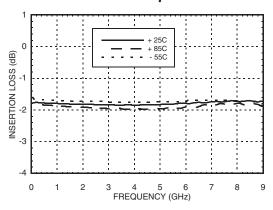
DOCUMENT FEEDBACK 🖳

Submit feedback for this data sheet.

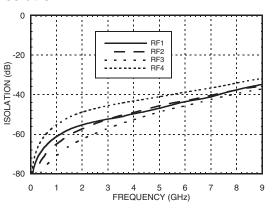


GaAs MMIC SP4T NON-REFLECTIVE SWITCH, DC - 8 GHz

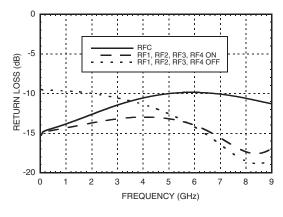
Insertion Loss vs. Temperature



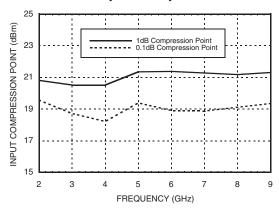
Isolation



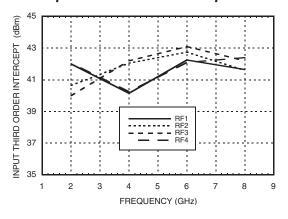
Return Loss



0.1 and 1 dB Input Compression Point



Input Third Order Intercept Point





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Absolute Maximum Ratings

Bias Voltage Range (Vee)	-7V
Control Voltage Range (A & B)	Vee -0.5V to +1V
Channel Temperature	150 °C
Thermal Resistance (Insertion Loss Path)	143 °C/W
Thermal Resistance (Terminated Path)	1,030 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
Maximum Input Power	+24 dBm
ESD Sensitivity (HBM)	Class 1A



Truth Table

Control Input		Signal Path State	
Α	В	RF COM to:	
High	High	RF1	
Low	High	RF2	
High	Low	RF3	
Low	Low	RF4	

Bias Voltage & Current

Vee Range = -5 Vdc ±10%			
Vee (V)	ldd (Typ) (mA)	Idd (Max) (mA)	
-5	3	6	

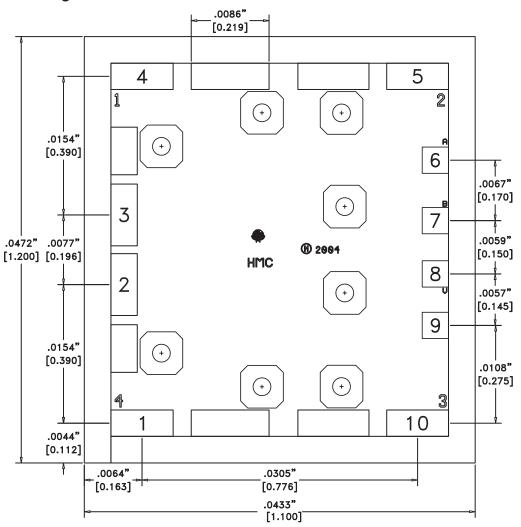
TTL/CMOS Control Voltages

State	Bias Condition
Low	-3V to 0 Vdc @ 60 uA Typ.
High	-5 to 4.2 Vdc @ 5 uA Typ.



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Outline Drawing



Die Packaging Information [1]

Standard	Alternate	
WP-2 (Waffle Pack)	[2]	

^[1] Refer to the "Packaging Information" section for die packaging dimensions.

NOTES:

- 1. DIMENSIONS IN INCHES [MILLIMETERS].
- 2. DIE THICKNESS IS 0.004".
- 3. TYPICAL BOND PAD IS 0.004" SQUARE.
- 4. TYPICAL BOND PAD SPACING IS 0.006" CENTER TO CENTER.
- 5. BOND PAD METALLIZATION: GOLD.
- 6. BACKSIDE METALLIZATION: GOLD.
- 7. BACKSIDE METAL IS GROUND.
- 8. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS.

^[2] For alternate packaging information contact Hittite Microwave Corporation.

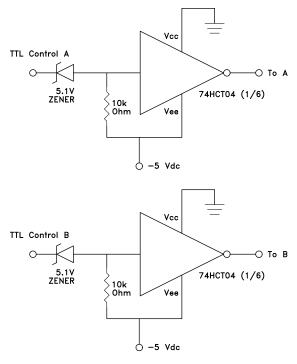


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Pad Descriptions

Pad Number	Function	Description	Interface Schematic	
1, 2, 3, 4, 5, 10	RF4, RFC, RF1, RF2, RF3	These pads are DC coupled and matched to 50 Ohms. Blocking capacitors are required.		
6	А	See truth table and control voltage table.	100K	
7	В	See truth table and control voltage table.	↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓	
8	Vee	Supply Voltage -5.0 Vdc ±10%		
9, Die Bottom	GND	Die bottom and pad must be connected to RF/DC ground.	GND	

TTL Interface Circuit

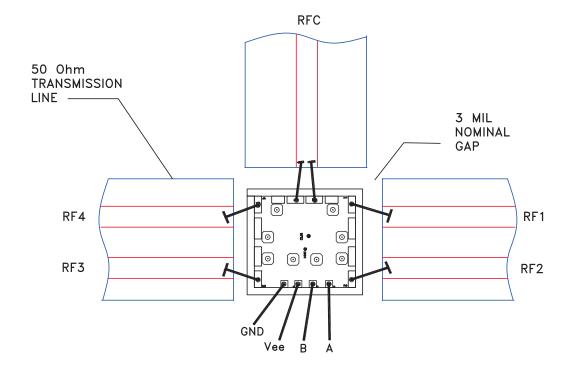


Control inputs A and B can be driven directly with TTL logic with -5 Volts applied to the HCT logic gates Vee pin and to Vee (pad) of the RF Switch.



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Assembly Diagram



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Analog Devices Inc.:

HMC344 HMC344ALP3E HMC344ALP3ETR